

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-60V	180mΩ@-10V	-1.7A
	270mΩ@-4.5V	

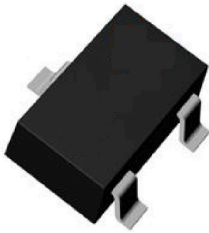
Feature

- Advanced trench process technology
- High density cell design for ultra low on-resistance

Application

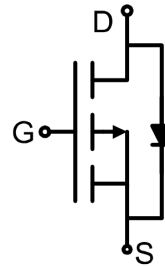
- Load Switch for Portable Devices
- DC/DC Converter

Package

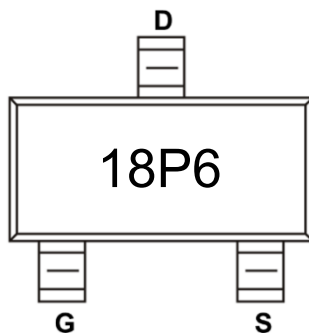


SOT-23

Circuit diagram



Marking



Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	-1.7	A
Pulsed Drain Current	I_{DM}	-6	A
Power Dissipation	P_D	1	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

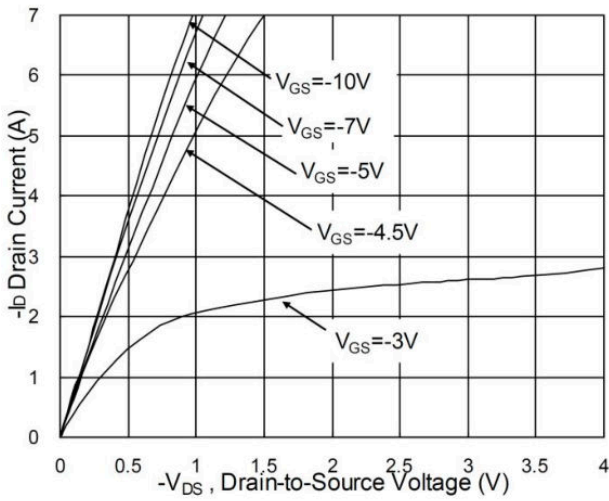
Electrical characteristics (T_A=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-60			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -48V, V_{GS} = 0V$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0		-2.5	V
Drain-source on-resistance ¹⁾	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -1.5A$			180	mΩ
		$V_{GS} = -4.5V, I_D = -1.0A$			270	
Dynamic characteristics²⁾						
Input Capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$		531		pF
Output Capacitance	C_{oss}			59		
Reverse Transfer Capacitance	C_{rss}			38		
Total Gate Charge	Q_g	$V_{DS} = -20V, V_{GS} = -4.5V, I_D = -1.5A$		4.6		nC
Gate-Source Charge	Q_{gs}			1.4		
Gate-Drain Charge	Q_{gd}			1.62		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -15V, V_{GS} = -10V, I_D = -1A, R_{GEN} = 3.3\Omega$		17.4		nS
Turn-on rise time	t_r			5.4		
Turn-off delay time	$t_{d(off)}$			37.2		
Turn-off fall time	t_f			2.4		
Source-Drain Diode characteristics						
Diode Forward voltage	V_{DS}	$V_{GS} = 0V, I_S = -1A$			-1.2	V

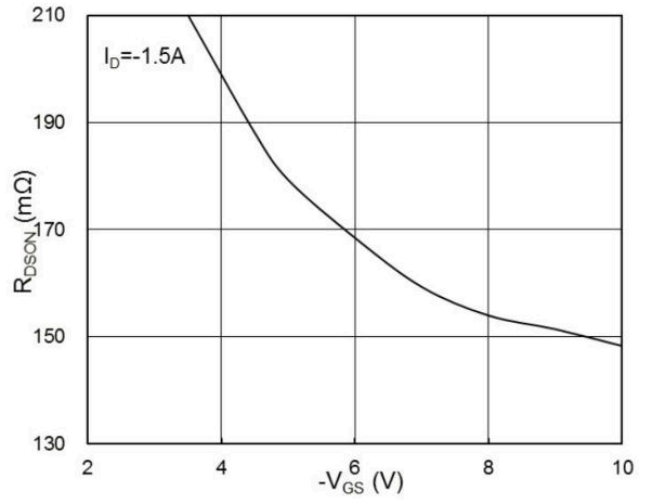
Notes:

- 1) Pulse Test: Pulse Width < 300μs, Duty Cycle ≤2%.
- 2) Guaranteed by design, not subject to production testing.

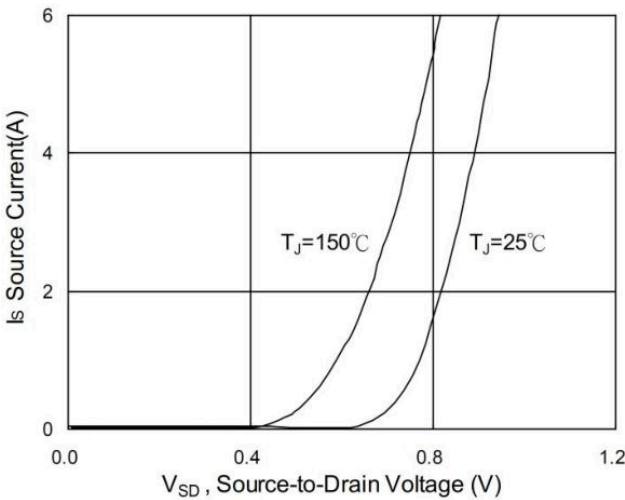
Typical Characteristics



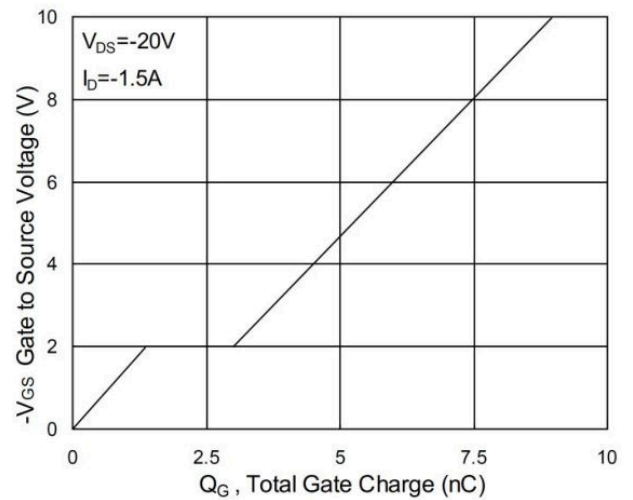
Output Characteristics



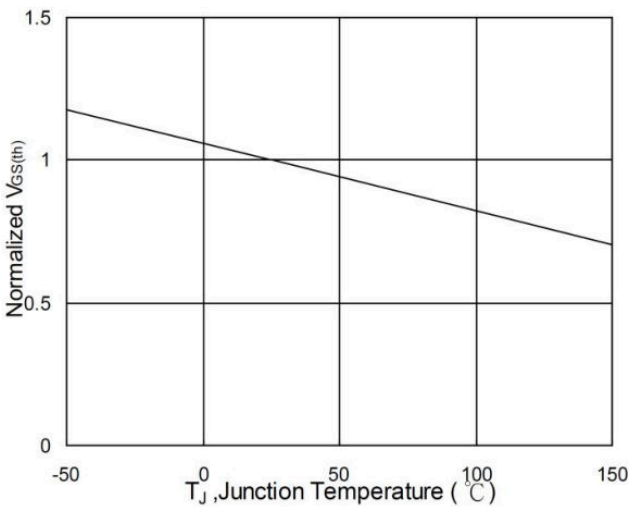
On-Resistance vs. Gate to Source Voltage



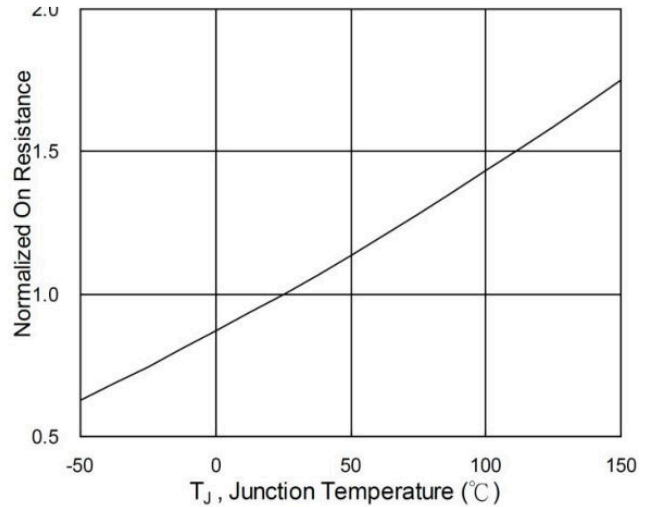
Forward Characteristics Of Reverse



Gate-Charge Characteristics

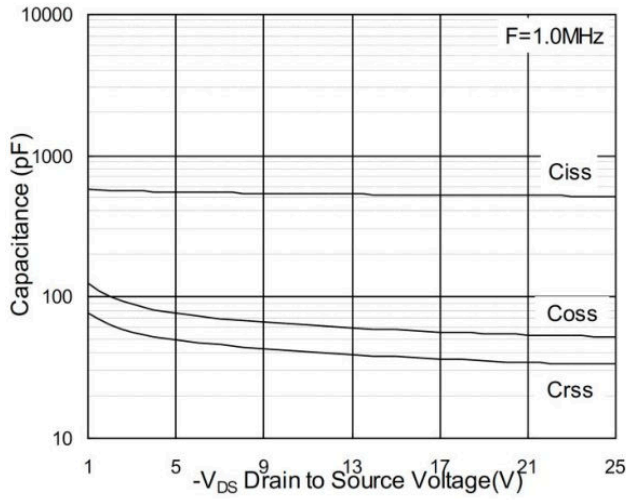


$V_{GS(th)}$ vs. T_J

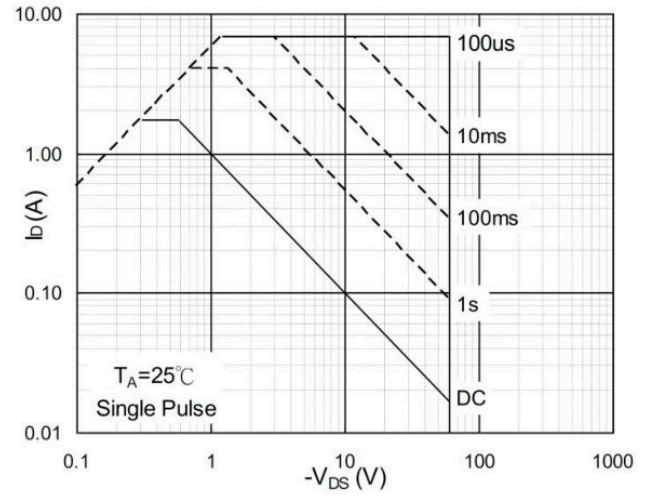


$R_{DS(on)}$ vs. T_J

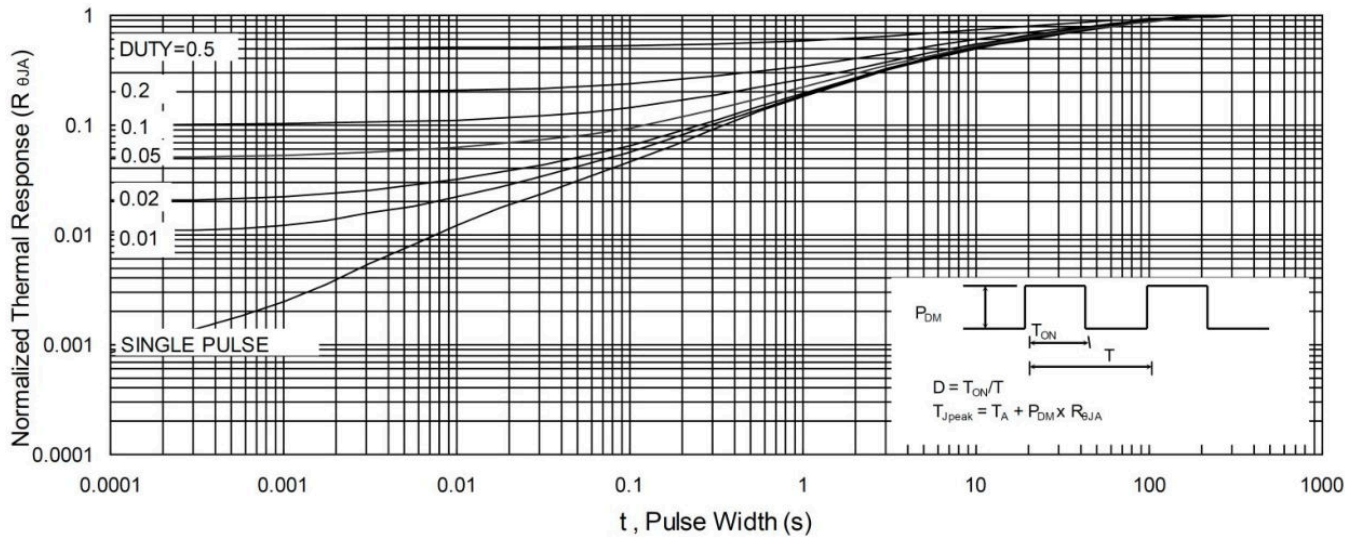
Typical Characteristics



Capacitance

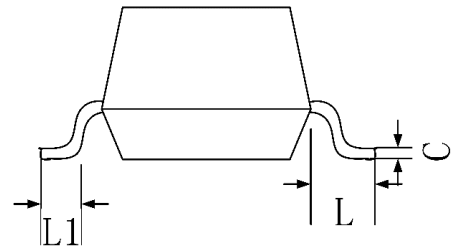
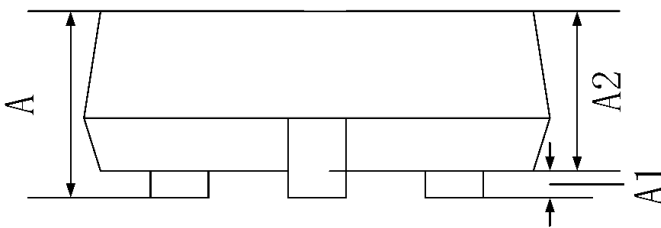
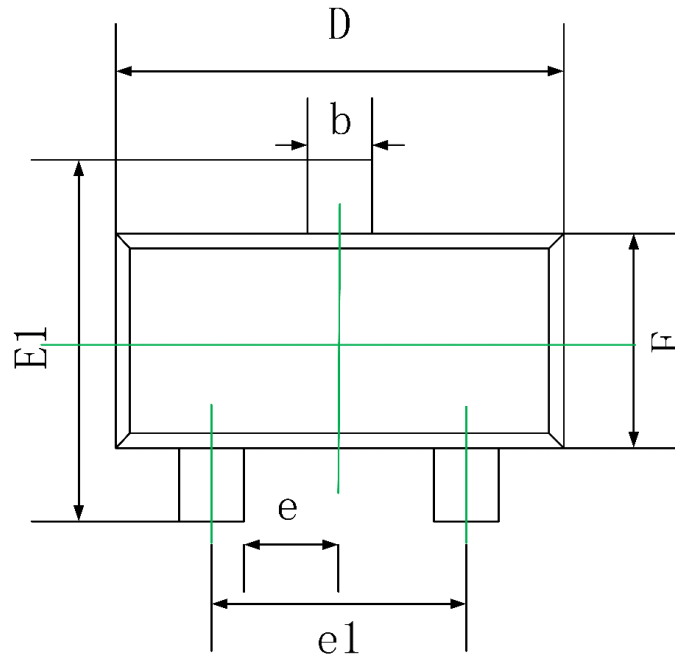


Safe Operating Area



Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [AnBon](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [FW216A-TL-2W](#) [FW231A-TL-E](#) [APT5010JVR](#) [NTNS3A92PZT5G](#)
[IRF100S201](#) [JANTX2N5237](#) [2SK2464-TL-E](#) [2SK3818-DL-E](#) [FCA20N60_F109](#) [FDZ595PZ](#) [STD6600NT4G](#) [FSS804-TL-E](#) [2SJ277-DL-E](#)
[2SK1691-DL-E](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MCH6646-TL-E](#) [TPCC8103,L1Q\(CM](#) [367-8430-0972-503](#) [VN1206L](#) [424134F](#)
[026935X](#) [051075F](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [751625C](#) [873612G](#) [IRF7380TRHR](#) [IPS70R2K0CEAKMA1](#)
[RJK60S3DPP-E0#T2](#) [RJK60S5DPK-M0#T0](#) [APT5010JVFR](#) [APT12031JFLL](#) [APT12040JVR](#) [DMN3404LQ-7](#) [NTE6400](#) [JANTX2N6796U](#)
[JANTX2N6784U](#) [JANTXV2N5416U4](#) [SQM110N05-06L-GE3](#) [SIHF35N60E-GE3](#) [2SK2614\(TE16L1,Q\)](#)